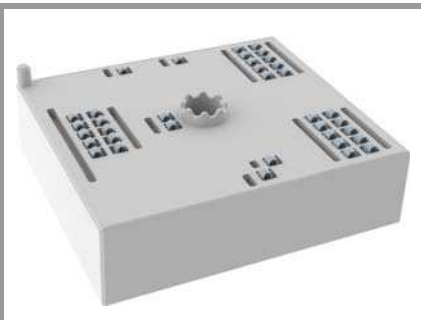


SKiiP 22GB17E4V1



MiniSKiiP® 2 Dual

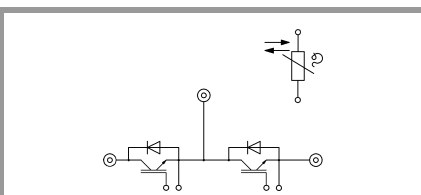
SKiiP 22GB17E4V1

Features

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)
- The creepage distance between T-Sensor and ground is 8mm

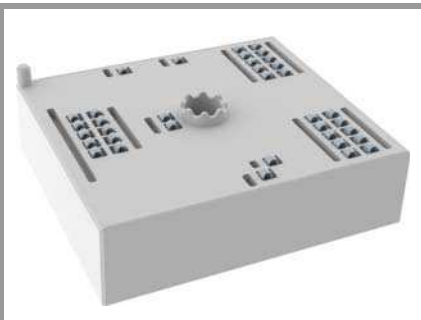


GB

| Absolute Maximum Ratings | | | | |
|--------------------------|---|---------------------------|-------------|------------------|
| Symbol | Conditions | | Values | Unit |
| Inverter - IGBT | | | | |
| V_{CES} | $T_j = 25^\circ\text{C}$ | | 1700 | V |
| I_C | $T_j = 175^\circ\text{C}$ | $T_s = 25^\circ\text{C}$ | 117 | A |
| | | $T_s = 70^\circ\text{C}$ | 95 | A |
| I_{Cnom} | | | 100 | A |
| I_{CRM} | $I_{CRM} = 3 \times I_{Cnom}$ | | 300 | A |
| V_{GES} | | | -20 ... 20 | V |
| t_{psc} | $V_{CC} = 1000\text{ V}$ | $T_j = 150^\circ\text{C}$ | 10 | μs |
| | $V_{GE} \leq 15\text{ V}$ | | | |
| | $V_{CES} \leq 1700\text{ V}$ | | | |
| T_j | | | -40 ... 175 | $^\circ\text{C}$ |
| Inverse - Diode | | | | |
| I_F | $T_j = 175^\circ\text{C}$ | $T_s = 25^\circ\text{C}$ | 91 | A |
| | | $T_s = 70^\circ\text{C}$ | 71 | A |
| I_{Fnom} | | | 100 | A |
| I_{FRM} | $I_{FRM} = 2 \times I_{Fnom}$ | | 200 | A |
| I_{FSM} | 10 ms, sin 180°, $T_j = 150^\circ\text{C}$ | | 580 | A |
| T_j | | | -40 ... 175 | $^\circ\text{C}$ |
| Module | | | | |
| $I_{t(RMS)}$ | $T_{terminal} = 80^\circ\text{C}$, 20 A per spring | | 200 | A |
| T_{stg} | | | -40 ... 125 | $^\circ\text{C}$ |
| V_{isol} | AC sinus 50 Hz, t = 1 min | | 2500 | V |

| Characteristics | | | | | | |
|------------------------|---|---------------------------|------|------|------|------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| Inverter - IGBT | | | | | | |
| $V_{CE(sat)}$ | $I_C = 100\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 1.90 | 2.20 | | V |
| | | $T_j = 150^\circ\text{C}$ | 2.30 | 2.60 | | V |
| V_{CE0} | chipelevel | $T_j = 25^\circ\text{C}$ | 0.8 | 0.9 | | V |
| | | $T_j = 150^\circ\text{C}$ | 0.7 | 0.8 | | V |
| r_{CE} | $V_{GE} = 15\text{ V}$ chipelevel | $T_j = 25^\circ\text{C}$ | 11 | 13 | | m Ω |
| | | $T_j = 150^\circ\text{C}$ | 16 | 18 | | m Ω |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}$, $I_C = 4\text{ mA}$ | | 5.2 | 5.8 | 6.4 | V |
| I_{CES} | $V_{GE} = 0\text{ V}$ $V_{CE} = 1700\text{ V}$ | $T_j = 25^\circ\text{C}$ | 0.1 | 0.3 | | mA |
| | | | | | | mA |
| C_{ies} | $V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$ | $f = 1\text{ MHz}$ | 9.00 | | | nF |
| C_{oes} | | $f = 1\text{ MHz}$ | 0.34 | | | nF |
| C_{res} | | $f = 1\text{ MHz}$ | 0.29 | | | nF |
| Q_G | - 8 V...+ 15 V | | 800 | | | nC |
| R_{Gint} | $T_j = 25^\circ\text{C}$ | | 7.5 | | | Ω |
| $t_{d(on)}$ | $V_{CC} = 900\text{ V}$ $I_C = 100\text{ A}$ | | 232 | | | ns |
| t_r | $R_{Gon} = 2\ \Omega$ | | 41 | | | ns |
| E_{on} | $R_{Goff} = 2\ \Omega$ | | 22.2 | | | mJ |
| $t_{d(off)}$ | $di/dt_{on} = 2892\text{ A}/\mu\text{s}$ | | 600 | | | ns |
| t_f | $di/dt_{off} = 665\text{ A}/\mu\text{s}$ $du/dt = 5490\text{ V}/\mu\text{s}$ | | 144 | | | ns |
| E_{off} | $V_{GE} = +15/-15\text{ V}$ $L_s = 25\text{ nH}$ | | 30.7 | | | mJ |
| $R_{th(j-s)}$ | per IGBT, $\lambda_{paste} = 0.8\text{ W}/\text{K} \cdot \text{m}$ | | 0.43 | | | K/W |

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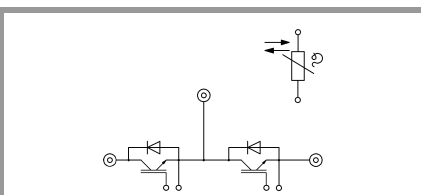
Features

- Trench IGBTs
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- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^{\circ}\text{C}$
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- The creepage distance between T-Sensor and ground is 8mm

| Characteristics | | | | | | |
|---------------------------|--|-----------------------------|------|---------------|------|---------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| Inverse - Diode | | | | | | |
| $V_F = V_{EC}$ | $I_F = 100 \text{ A}$ $V_{GE} = 0 \text{ V}$ chipelevel | $T_j = 25^{\circ}\text{C}$ | | 2 | 2.4 | V |
| | | $T_j = 150^{\circ}\text{C}$ | | 2.2 | 2.6 | V |
| V_{F0} | chipelevel | $T_j = 25^{\circ}\text{C}$ | | 1.3 | 1.6 | V |
| | | $T_j = 150^{\circ}\text{C}$ | | 1.1 | 1.2 | V |
| r_F | chipelevel | $T_j = 25^{\circ}\text{C}$ | | 6.8 | 8.4 | m Ω |
| | | $T_j = 150^{\circ}\text{C}$ | | 11 | 14 | m Ω |
| I_{RRM} | $I_F = 100 \text{ A}$ | | | 165 | | A |
| Q_{rr} | $di/dt_{off} = 3753 \text{ A}/\mu\text{s}$ | | | 32.5 | | μC |
| E_{rr} | $V_{GE} = -15 \text{ V}$ $V_{CC} = 900 \text{ V}$ | | | 20.9 | | mJ |
| $R_{th(j-s)}$ | per Diode, $\lambda_{paste}=0.8 \text{ W}/\text{K}^*\text{m}$ | | | 0.7 | | K/W |
| Module | | | | | | |
| L_{CE} | | | | 20 | | nH |
| M_s | to heat sink | | 2 | | 2.5 | Nm |
| w | | | | 50 | | g |
| Temperature Sensor | | | | | | |
| R_{100} | $T_c=100^{\circ}\text{C}$ ($R_{25}=5 \text{ k}\Omega$) | | | $493 \pm 5\%$ | | Ω |
| $B_{25/85}$ | $R_{(T)}=R_{25} \cdot \exp[B_{25/85} \cdot (1/T - 1/298)]$, [T]=K | | | 3420 | | K |



GB

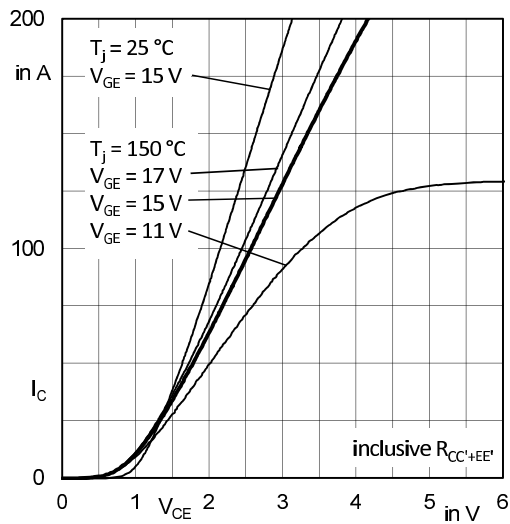


Fig. 1: Typ. output characteristic, inclusive $R_{CC+EE'}$

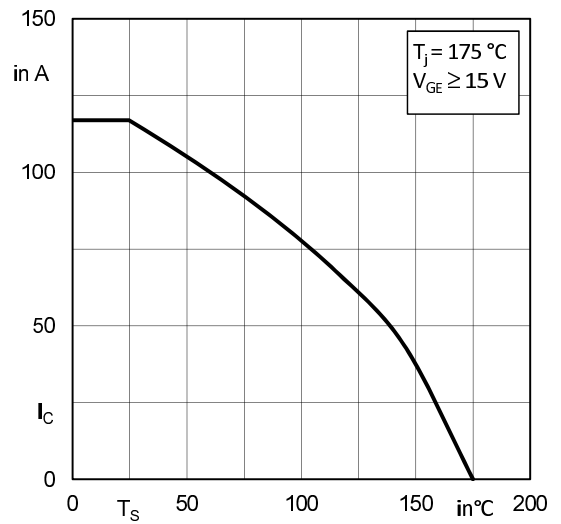


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

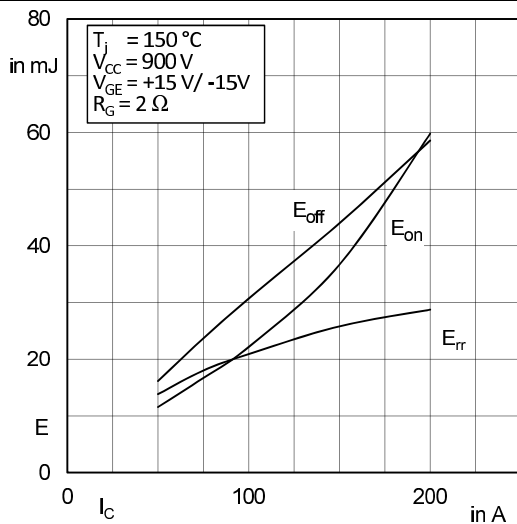


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

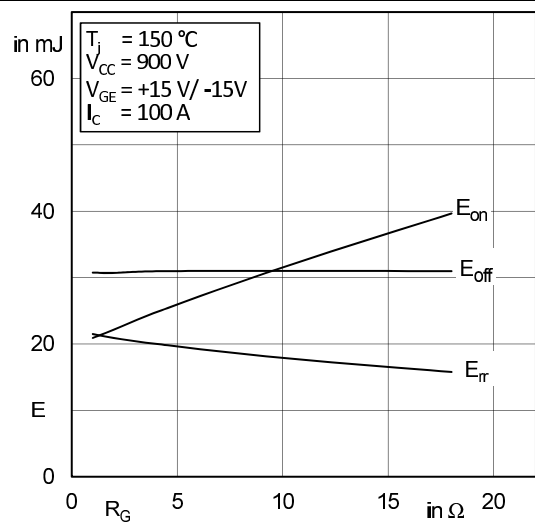


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

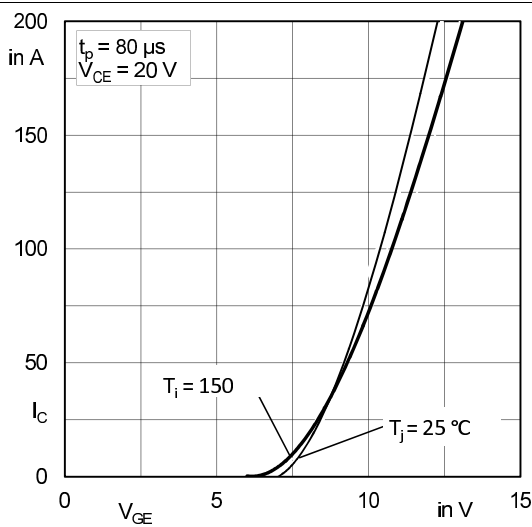


Fig. 5: Typ. transfer characteristic

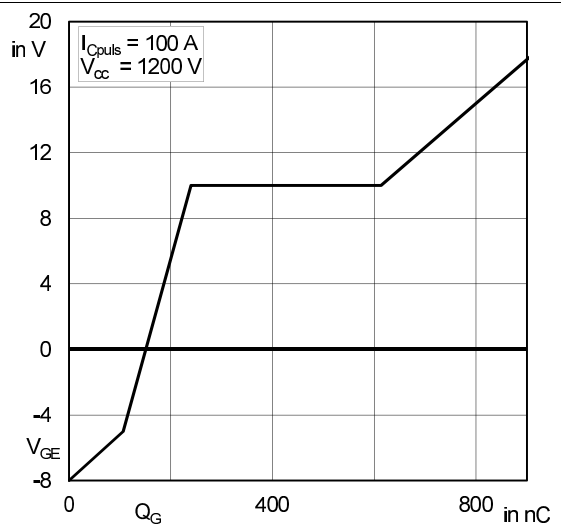


Fig. 6: Typ. gate charge characteristic

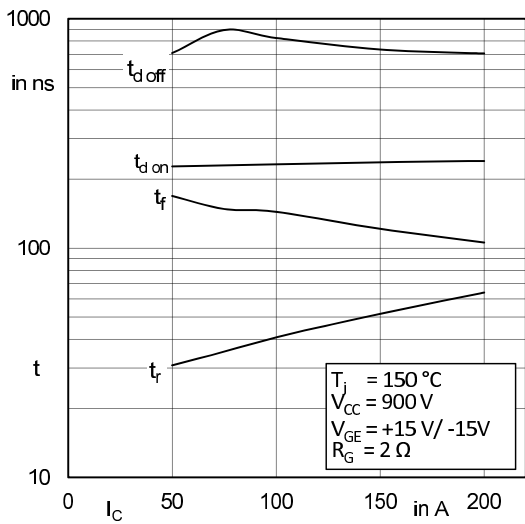


Fig. 7: Typ. switching times vs. I_C

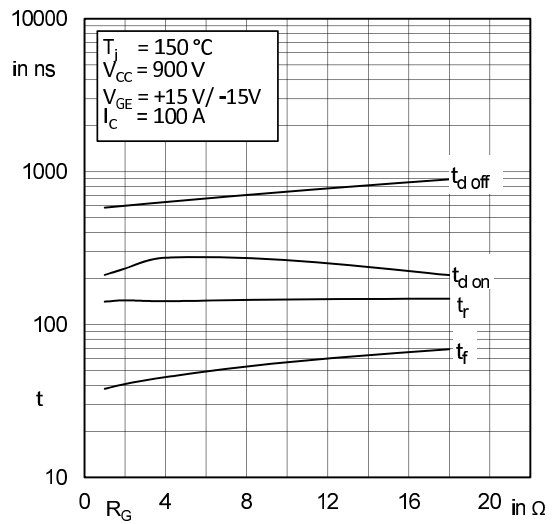


Fig. 8: Typ. switching times vs. gate resistor R_G

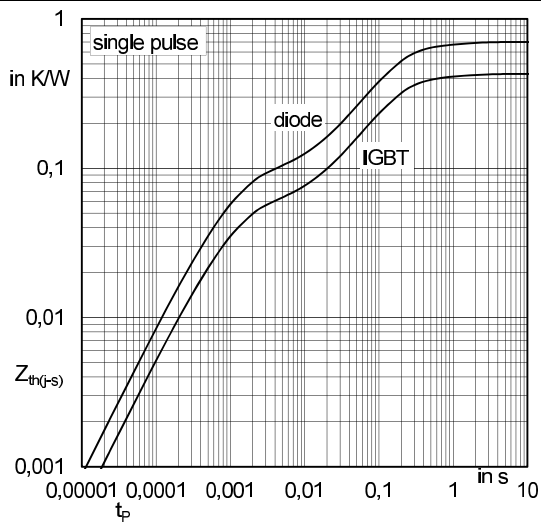


Fig. 9: Transient thermal impedance of IGBT and Diode

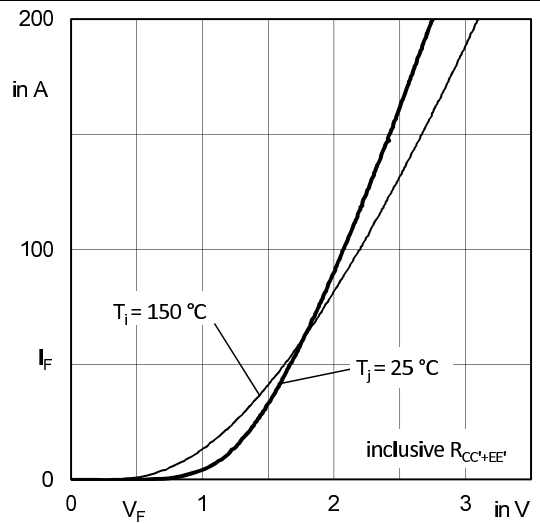


Fig. 10: CAL diode forward characteristic

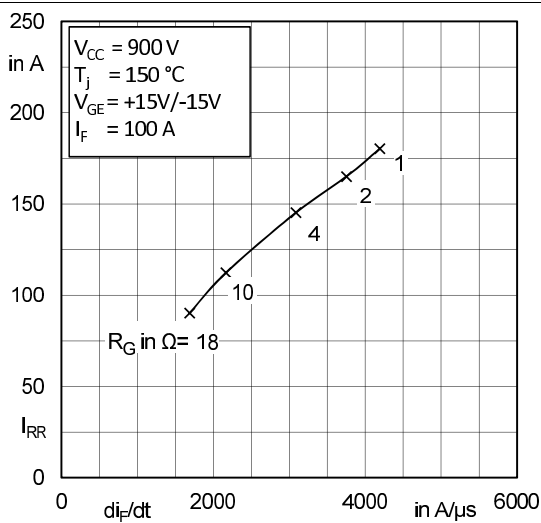


Fig. 11: Typ. CAL diode peak reverse recovery current

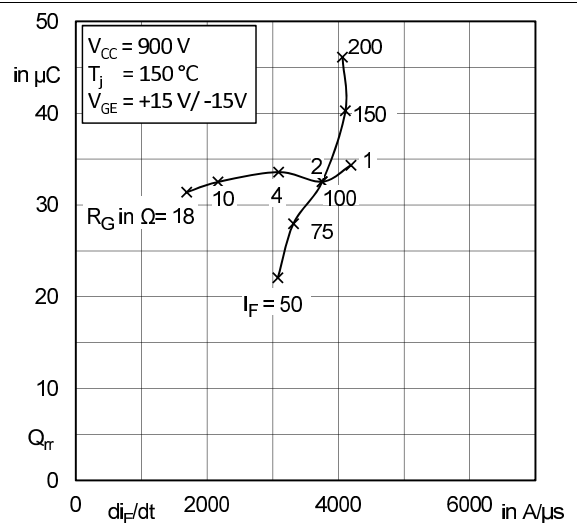
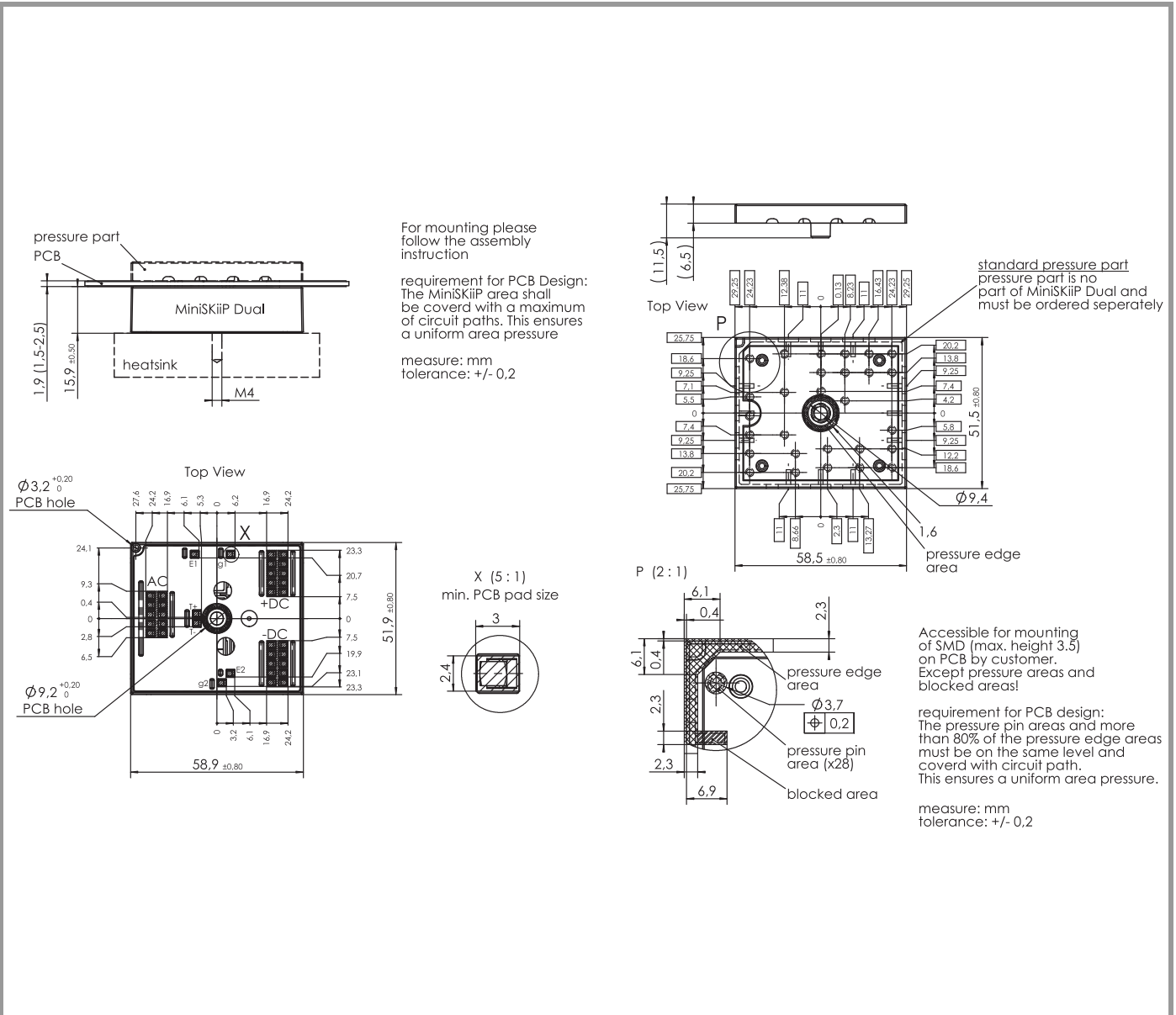
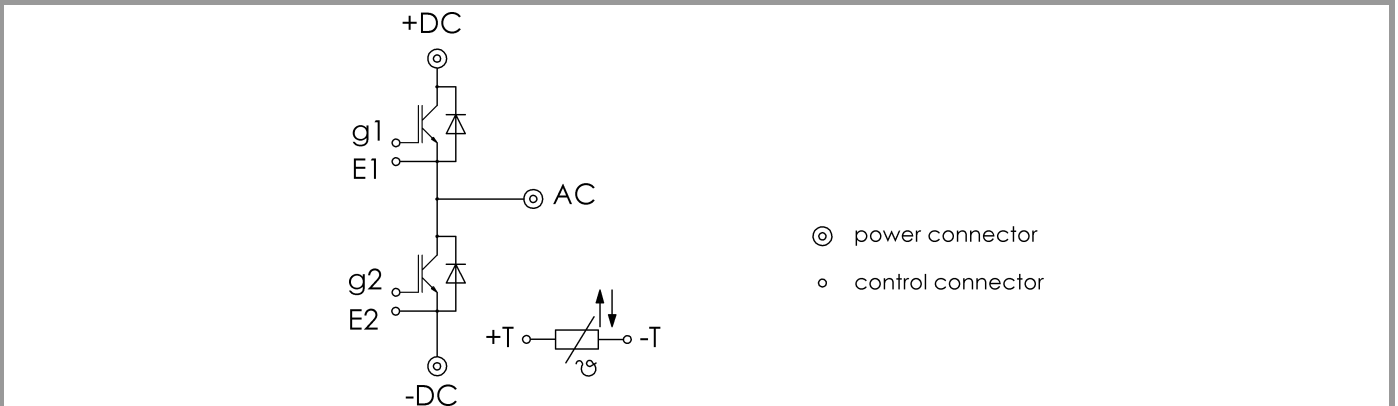


Fig. 12: Typ. CAL diode recovery charge

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pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.